

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the applications:

Listing of Claims:

Claim 1 (Currently amended). An electrostatic discharge (ESD) protection device, comprising:

- a semiconductor bulk of a first conductivity type;

- a first doped region of a second conductivity type formed in said semiconductor bulk;

- a second doped region of a second conductivity type formed in said semiconductor bulk;

- a channel region formed between said first doped region and said second region, and said channel region comprises a first part, a second part and a third part; wherein said first part and said third part are the different ends of said channel region, and said second part is located between said first part and said third part;

- a first gate segment formed only over a first part of said channel region;

- a first field-oxide stripe formed only over a second part of said channel region;

and

- a first end of said first gate segment overlaps said first field-oxide stripe.

Claim 2 (Canceled).

Claim 3 (Previously presented). A device according to Claim 1, wherein said first and second parts form a first continuous portion of said channel.

Claim 4 (Previously presented). A device according to Claim 1, wherein said first gate segment and said first field-oxide stripe are substantially collinear.

Claim 5 (Previously presented). A device according to Claim 1, wherein said first gate

segment comprises a polysilicon element over an oxide layer.

Claim 6 (Previously presented). A device according to Claim 1, further comprising a plurality of islands formed over said bulk and being encircled by said first doped region .

Claim 7 (Previously presented) A device according to Claim 6, wherein said plurality of islands comprises a first and second arrays of islands; said first array of islands comprises polysilicon-over-oxide islands; and said second array of islands comprises field-oxide islands .

Claim 8 (Previously presented) A device according to Claim 7, wherein said first array of islands is closer to said channel region than said second array of islands.

Claim 9 (Previously presented) A device according to Claim 7, further comprising a second gate segment formed over a third part of said channel region; and a first end of said second gate segment overlaps said first field-oxide stripe.

Claim 10 (Canceled)

Claim 11(Previously presented) A device according to Claim 9, wherein said second and third parts form a second continuous portion of said channel.

Claim 12 (Previously presented) A device according to Claim 1, wherein said first doped region couples to a pad.

Claim 13 (Previously presented) A device according to Claim 1, wherein said second doped region couples to a power bus.

Claim 14 (Previously presented) A device according to Claim 1, wherein said channel region comprising a split-channel region and a non-split-channel region; and further

comprising a second gate segment;

said split channel region including a first and a second sub-channel regions spaced apart from each other; wherein said first sub-channel region being adjacent to said first doped region and second sub-channel region being adjacent to said second doped region;

said first gate segment formed over said first sub-channel region;

said second gate segment formed over said second sub-channel region;

said first field-oxide stripe formed over said non-split-channel region .

Claim 15 (Previously presented) A device according to Claim 14, wherein said first and said second gate segments are substantially parallel to each other.

Claim 16 (Previously presented) A device according to Claim14, wherein said first gate segment, said second gate segment and said first field-oxide stripe are substantially parallel to each other.

Claim 17 (Previously presented) A device according to Claim 14, wherein said split channel region is connected to said non-split channel region to form a continuous channel region .

Claim 18 (Previously presented) A device according to Claim14, wherein said first gate segment comprises a polysilicon element over an oxide layer .

Claim 19 (Previously presented) A device according to Claim 14, wherein said second gate segment comprises a polysilicon element over an oxide layer.

Claim 20 (Currently amended) A device according to Claim 14, wherein said first gate segment have a first end overlapping said first field-oxide stripe; and said second gate ~~second~~ gate segment have a second end overlapping said first field-oxide stripe.

Claim 21 (Canceled)

Claim 22 (Previously presented) A device according to Claim 14, further comprising a plurality of islands formed over said bulk and being encircled by said first doped region.

Claim 23 (Canceled)

Claim 24 (Previously presented) A device according to Claim 14, wherein said first doped region coupling to a pad.

Claim 25 (Previously presented) A device according to Claim 14, wherein said second doped region coupling to a power bus.

Claim 26 (Currently amended) An electrostatic discharge (ESD) protection device, comprising:

- a semiconductor bulk of a first conductivity type;

- a first doped region of second conductivity type formed in said semiconductor bulk;

- a second doped region of a second conductivity type formed in said semiconductor bulk;

- a channel region formed between said first and said second doped regions and said channel region comprises a first part, a second part and a third part, wherein said first part and said third part are the different ends of said channel region, and said second part is located between said first part and said third part;

- a first gate segment formed only over a first part of said channel region;

- a first field-oxide stripe formed only over a second part of said channel region;

- a first end of said first gate segment overlaps said first field-oxide stripe;

- a first and a second arrays of islands formed over said bulk and being encircled by said first doped region; wherein

- said first array of islands comprising polysilicon-over-oxide islands;

- said second array of islands comprising field-oxide islands; and

said first array of islands being closer to said channel region than said second array of islands.